ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE5417 thru NTE5419
Silicon Controlled Rectifier (SCR)
10 Amp

Absolute Maximum Ratings:

Repetitive Peak Reverse Voltage (T_C = +110°C), V_{RRM}
- NTE5417 . . . . . 200V
- NTE5418 . . . . . 400V
- NTE5419 . . . . . 600V

Repetitive Peak Off–State Voltage (T_C = +110°C), V_{DRM}
- NTE5417 . . . . . 200V
- NTE5418 . . . . . 400V
- NTE5419 . . . . . 600V

RMS On–State Current (T_C = +80°C, Conduction Angle of 180°), $I_{T(RMS)}$ 10A

Peak Surge (Non–Repetitive) On–State Current (One Cycle at 50 or 60Hz), I_{TSM} 100A

Peak Gate–Trigger Current (3μs Max), I_{GTM} 1A

Peak Gate–Power Dissipation ($I_{GT} \le I_{GTM}$), P_{GM} 16W

Average Gate Power Dissipation, $P_{G(AV)}$ 500mW

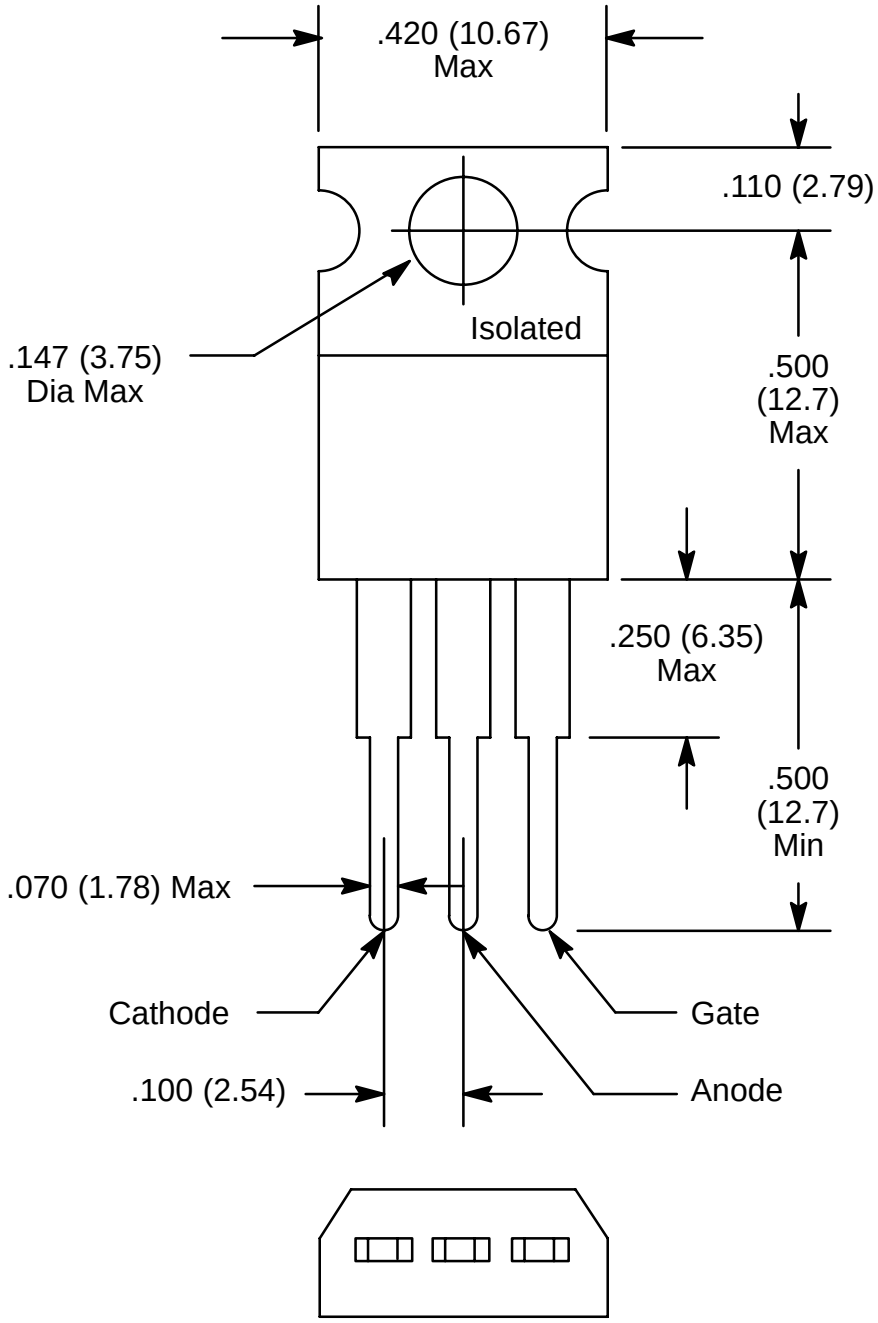
Operating Temperature Range, T_{opr} . . . . . –40° to +110°C

Storage Temperature Range, T_{stg} . . . . . –40° to +150°C

Typical Thermal Resistance, Junction–to–Case, R_{thJC} . . . . . 2.5°C/W

Electrical Characteristics: (T_C = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Peak Off–State Current	I_{RRM}	V_{RRM} = Max, V_{DRM} = Max, T_C = +110°C	–	–	0.5	mA
	I_{DRM}		–	–	0.5	mA
Maximum Peak On–State Voltage	V_{TM}	I_T = 10A	–	–	1.8	V
DC Holding Current	I_{HOLD}	Gate Open	–	–	30	mA
DC Gate–Trigger Current	I_{GT}	V_D = 6VDC, R_L = 60Ω	–	–	25	mA
DC Gate–Trigger Voltage	V_{GT}	V_D = 6VDC, R_L = 60Ω	–	–	1.5	V
Gate Controlled Turn–On Time	t_{gt}	I_{GT} = 100mA	–	2.5	–	μs
Critical Rate of Off–State Voltage	dv/dt (critical)	Gate Open, T_C = +100°C	–	200	–	V/μs


.420 (10.67)
Max
.110 (2.79)
Isolated
.147 (3.75)
Dia Max
.500
(12.7)
Max
.250 (6.35)
Max
.500
(12.7)
Min
.070 (1.78) Max
Cathode
Gate
.100 (2.54)
Anode